



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Transistors

2SA1579 TRANSISTOR (PNP)

FEATURES

- High breakdown voltage. ($BV_{CEO} = -120V$)
- Complements the 2SC4102

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector- Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Dissipation	100	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-100V, I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-1mA$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12V, I_C=-2mA, f=30MHz$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-12V, I_E=0, f=1MHz$		3.2		pF

CLASSIFICATION OF h_{FE}

Rank	R	S
Range	180-390	270-560
Marking	RR	RS

Typical Characteristics

2SA1579

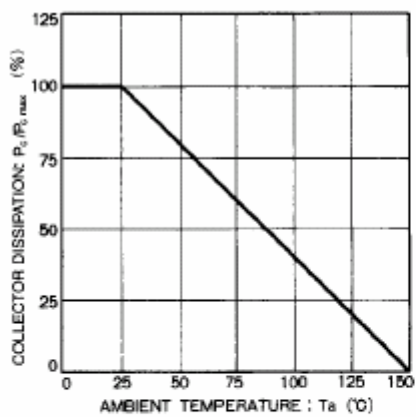


Figure 1

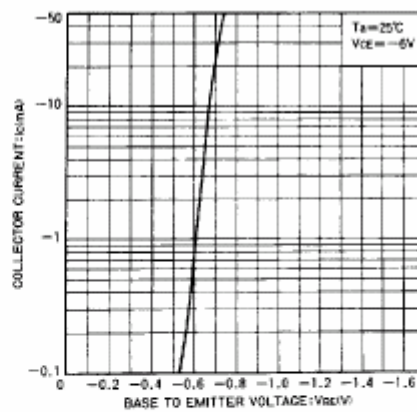


Figure 2

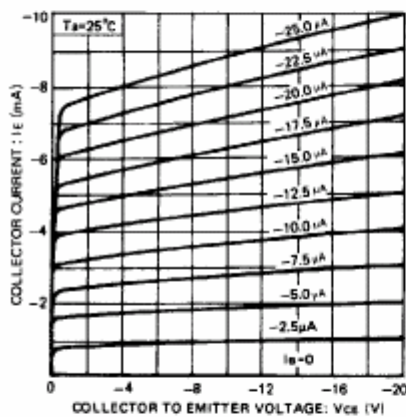


Figure 3

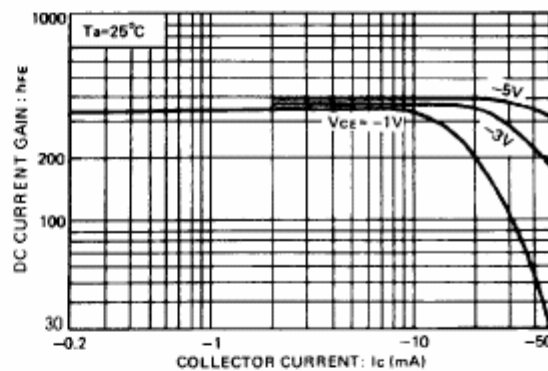


Figure 4

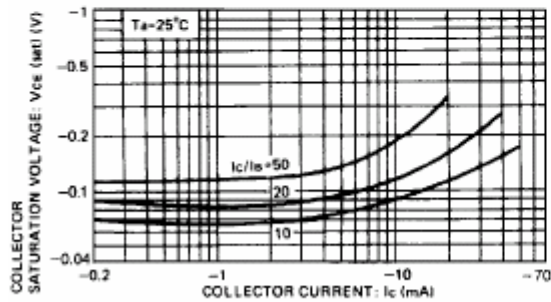


Figure 5

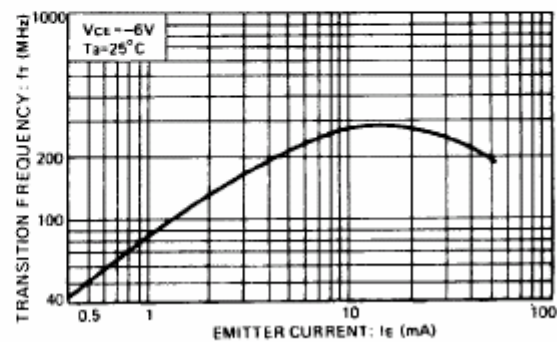


Figure 6

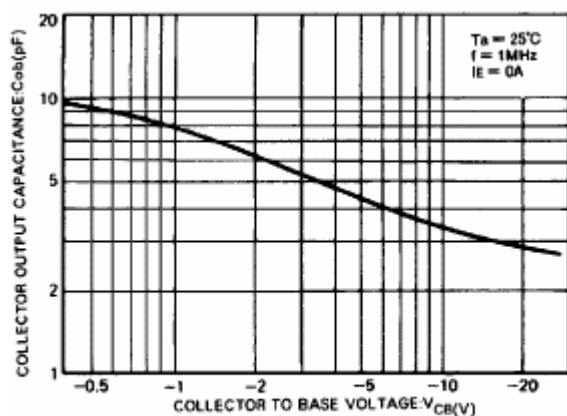


Figure 7

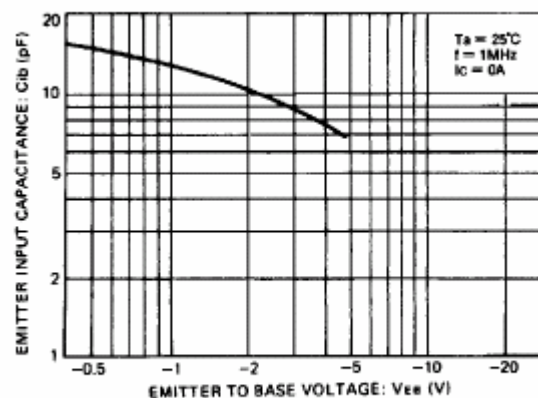


Figure 8